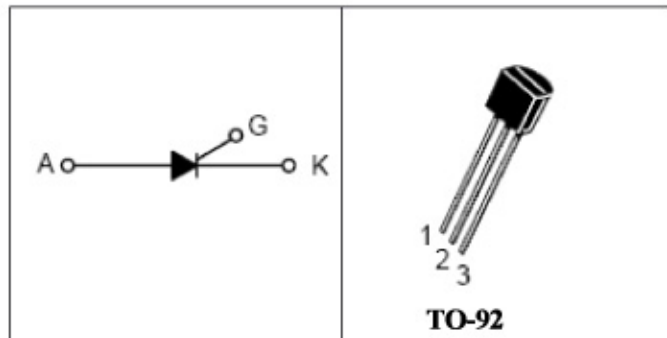




# 绍兴怡华电子科技有限公司

## ■ 主要特点:

符号	数值	单位
$I_T$ (RMS)	0.8	A
$V_{DRM}/V_{RRM}$	400&600	V
$I_{GT}$ (Q1)	200	$\mu A$



## ■ 用途:

PCR406 单向可控硅系列适用于一般交流开关电路, 如: 固态继电器, 感应马达启动控制, 调温控制, 调光控制, 调速控制... 等.

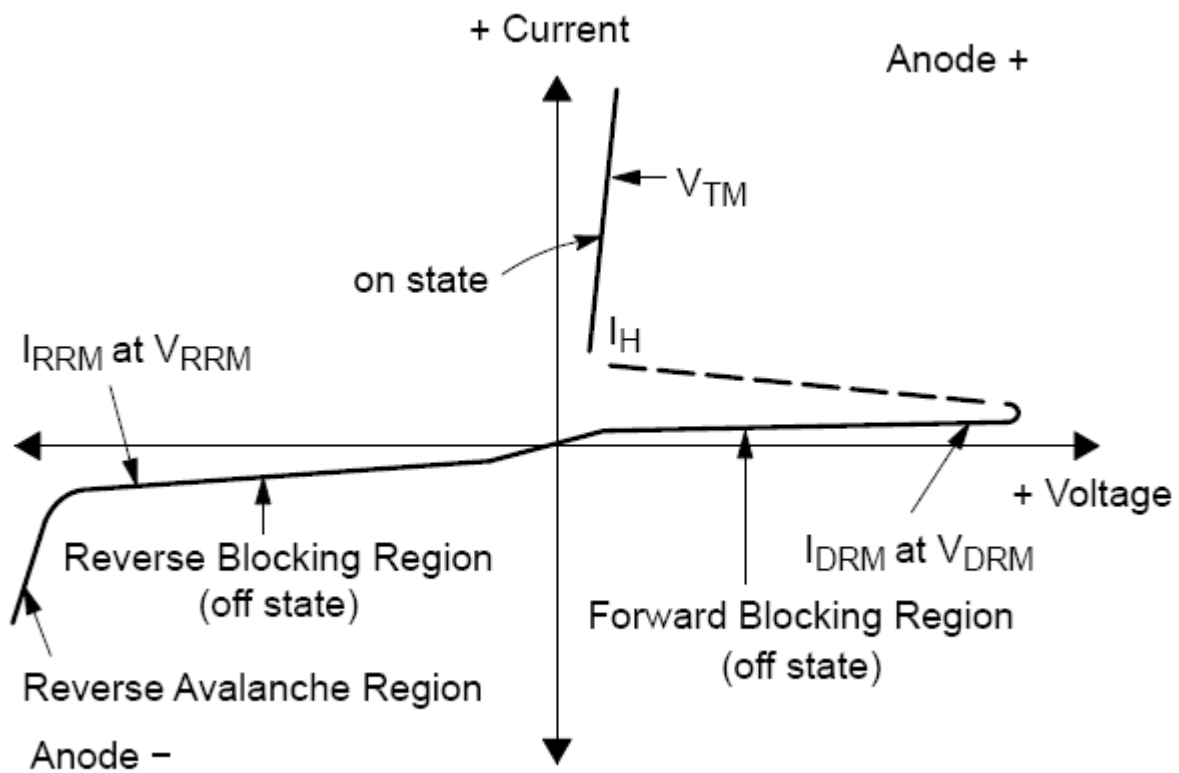
## ■ 极限值:

符号	参数		数值	单位
$I_{T(RMS)}$	RMS 通态电流	$T_C=80^\circ C$	0.8	A
$I_{TSM}$	通态峰值浪涌电流	$F=60Hz, T_J = 25^\circ C$	10	A
$I^2t$	$I^2t$ 耗散值	$t=8.3ms$	0.415	$A^2s$
$di/dt$	通态电流上升值	$F=120Hz, T_J=125^\circ C$	50	$A/\mu s$
$I_{GM}$	门极峰值电流	$TP=1.0\mu s, T_A=25^\circ C$	2	A
$P_{G(AV)}$	平均门极耗散功率	$T_A=25^\circ C, t=8.3ms$	0.1	W



■ 可控硅电压电流特性:

Symbol	Parameter
$V_{DRM}$	Peak Repetitive Off State Forward Voltage
$I_{DRM}$	Peak Forward Blocking Current
$V_{RRM}$	Peak Repetitive Off State Reverse Voltage
$I_{RRM}$	Peak Reverse Blocking Current
$V_{TM}$	Peak on State Voltage
$I_H$	Holding Current



■ 特性曲线:

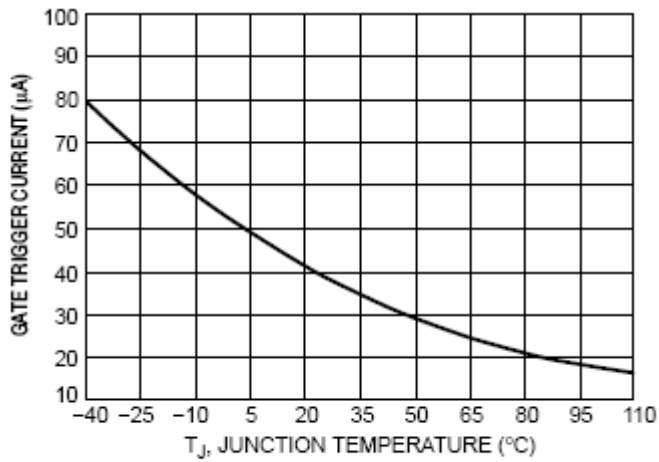


Figure 1. Typical Gate Trigger Current versus Junction Temperature

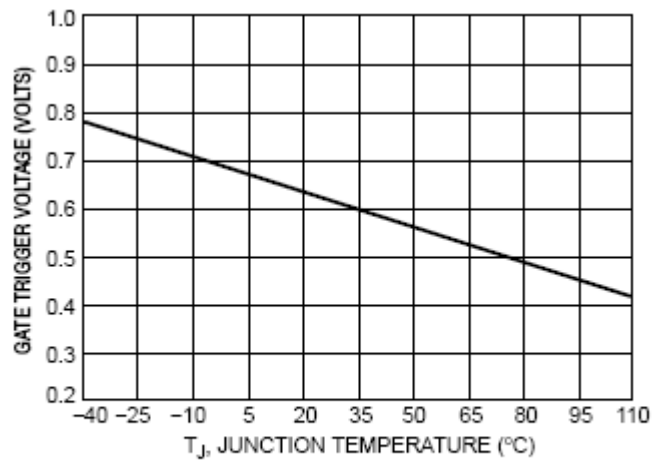


Figure 2. Typical Gate Trigger Voltage versus Junction Temperature

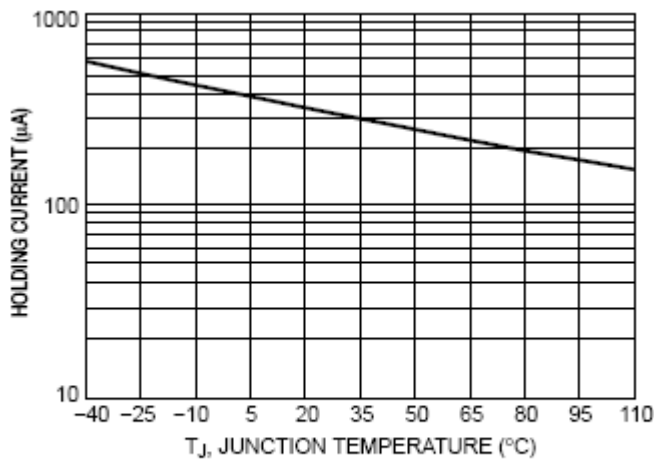


Figure 3. Typical Holding Current versus Junction Temperature

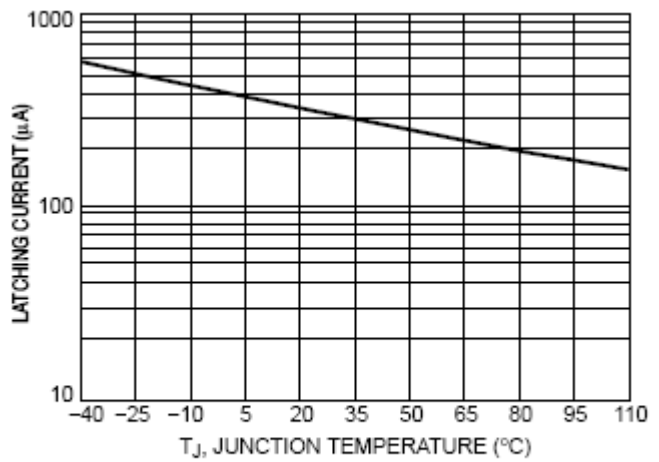


Figure 4. Typical Latching Current versus Junction Temperature

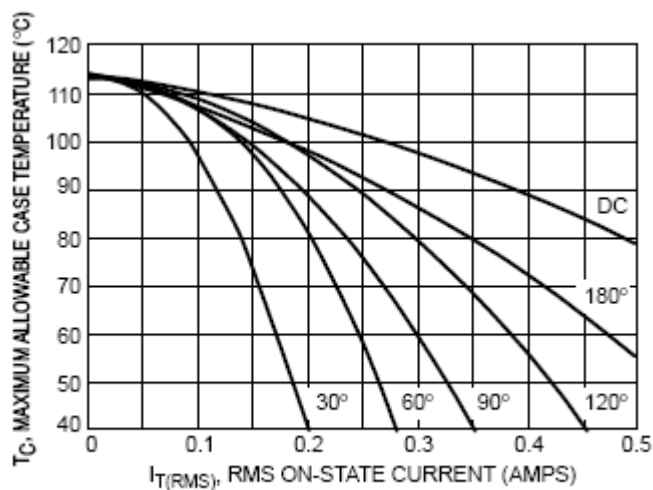


Figure 5. Typical RMS Current Derating

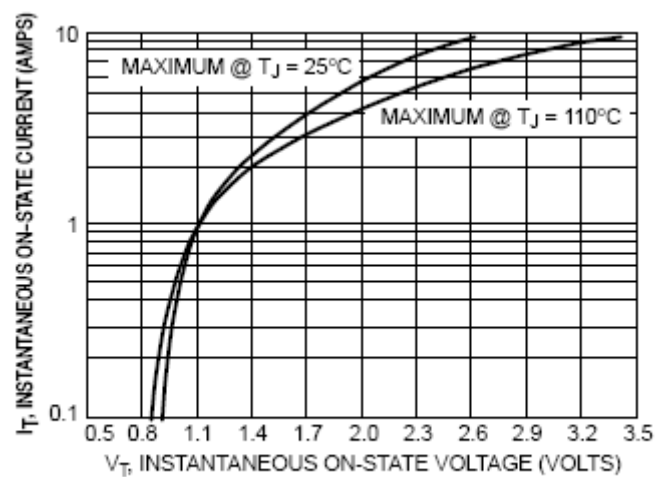


Figure 6. Typical On-State Characteristics

